

	Type	L #	Hits	Search Text	Dbs	Time Stamp	Comments	Error Definition	Error rs
1	BRS	L1	162	((zno or (zinc adj oxide)) near (insulat\$))	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 11:55		Truncation Overflow. Return string from Server is: 5.41008.1	1
2	BRS	L2	9	L1 and (trench or hole)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 12:46			0
3	BRS	L3	2	((zno or (zinc adj oxide)) with trench) and barrier	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 11:57			0
4	BRS	L4	5	((zno or (zinc with oxide)) same trench) and barrier	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 12:03			0
5	BRS	L5	279	((zno or ((conductive or zinc with oxide)) same trench) and (barrier or Tin or titanium)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 12:34			0
6	BRS	L6	25	L5 and (zinc or zn)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 12:47			0
7	BRS	L7	1950	phosphor same (trench or hole)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 12:47			0
8	BRS	L8	182	L7 and (zinc or zn)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 12:53			0

	Type	L #	Hits	Search Text	Dbs	Time Stamp	Comments	Error Definition	Error Is
9	BRS	L9	29	L8 and barrier	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 12:48			0
10	BRS	L10	1420	barrier with (zinc or zn)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 12:53			0
11	BRS	L11	1503	barrier with (zinc or zn or zno)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 12:53			0
12	BRS	L12	59	barrier near (zinc or zn or zno)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 13:03			0
13	BRS	L13	2243	(trench or hole) and ((zinc adj ox\$) or (zn near o) or zno)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 13:05		Truncation Overflow. Return string from Server is: 5'44328.4	1
14	BRS	L14	2364	(trench or hole) and ((zinc adj ox\$) or (zn with o) or zno)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 13:06		Truncation Overflow. Return string from Server is: 5'44328.4	1
15	BRS	L15	83	trench and ((zinc adj ox\$) or (zn with o) or zno)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 13:13		Truncation Overflow. Return string from Server is: 5'44328.4	1
16	IS&R	L16	1	("6211073").PN.	USPAT	2001/10/19 13:44			0
17	IS&R	L17	1	("5851849").PN.	USPAT	2001/10/19 13:46			0
18	IS&R	L18	0	("L14 not 115").PN.	USPAT	2001/10/19 13:47			0

Type	L #	Hits	Search Text	Dbs	Time Stamp	Comments	Error Definition	Errors
19 BRS	L19	2281	L14 not 115	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 13:47			0
20 BRS	L20	383	L19 and barrier	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 13:57			0
21 IS&R	L21	1	("5383088").FN.	USPAT	2001/10/19 13:57			0

	Type	L #	Hits	Search Text	Dbs	Time Stamp	Comments	Error Definition	Error ts
1	BRS	L1	162	((zno or (zinc adj oxide)) near (insulat\$))	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 11:55		Truncation Overflow. Return string from Server is: 5'41008'1	1
2	BRS	L2	9	L1 and (trench or hole)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 12:46			0
3	BRS	L3	2	((zno or (zinc adj oxide)) with trench) and barrier	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 11:57			0
4	BRS	L4	5	((zno or (zinc with oxide)) same trench) and barrier	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 12:03			0
5	BRS	L5	279	((zno or ((conductive or zinc) with oxide)) same trench) and (barrier or Tin or titanium)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 12:34			0
6	BRS	L6	25	L5 and (zinc or zn)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 12:47			0
7	BRS	L7	1950	phosphor same (trench or hole)	USPAT; US-PGPU B: EPO; JFO; DERWENT ; IBM TDB	2001/10/19 12:47			0
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10 BRS	L10	1420	Barrier with (zinc or zn)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 12:53			0
11 BRS	L11	1503	Barrier with (zinc or zn or zno)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 12:53			0
12 BRS	L12	59	Barrier near (zinc or zn or zno)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 13:03			0
13 BRS	L13	2243	(trench or hole) and ((zinc adj oxs) or (zn near o) or zno)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 13:05		Truncation Overflow. Return string from Server is: 5'44328'4	1
14 BRS	L14	2364	(trench or hole) and ((zinc adj oxs) or (zn with o) or zno)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 13:06		Truncation Overflow. Return string from Server is: 5'44328'4	1
15 BRS	L15	83	trench and ((zinc adj oxs) or (zn with o) or zno)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 13:13		Truncation Overflow. Return string from Server is: 5'44328'4	1
16 IS&R	L16	1	("6211073").PN.	USPAT	2001/10/19 13:44			0
17 IS&R	L17	1	("5851849").PN.	USPAT	2001/10/19 13:46			0
18 IS&R	L18	0	("L14 not 115").PN.	USPAT	2001/10/19 13:47			0

Type	L #	Hits	Search Text	Dbs	Time Stamp	Comments	Error Definition	Errors
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20 BRS	L20	383	L19 and barrier	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 13:57			0
21 IS&R	L21	1	("5383088").PN.	USPAT	2001/10/19 13:57			0
22 BRS	L22	8	257/767.ccls. and (zno or (zinc adj oxide))	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 14:05			0
23 BRS	L23	14	257/763.ccls. and (zno or (zinc adj oxide))	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 14:15			0
24 BRS	L24	16	257/751.ccls. and (zno or (zinc adj oxide))	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 15:08			0
25 BRS	L25	0	257/760.ccls. and (zno or (zinc adj oxide))	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 15:09			0
26 BRS	L26	10	257/758.ccls. and (zno or (zinc adj oxide))	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 15:09			0
27 BRS	L27	4	438/622.ccls. and (zno or (zinc adj oxide))	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/19 15:10			0

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US Full Image

Detailed Description Text - DETX (42):

An alternative embodiment of the method of this invention involves precoating the intermediate with a thin, for example approximately 100 angstroms (A) of high resistivity material suitable as a diffusion barrier before the anodic etching process. Suitable materials include (optionally doped with Al, In, Ga, or B); $\text{SnO}_{2.2}$ (doped with F or Sb); $\text{CdSnO}_{3.4}$; $\text{TiO}_{2.2}$ (doped with F), and $\text{SrTiO}_{3.2}$. The alternative process is particularly preferred since a tin oxide or layer is generally necessary as a to diffusion of indium from a subsequently sputter deposited indium-tin oxide (ITO) layer. The advantage of precoating with a thin oxide layer such as tin dioxide or zinc oxide prior to anodic etching is to protect the amorphous silicon from oxidation to silicon dioxide. Thus, the formation of an electrical insulating barrier of silicon dioxide is prevented and a

U.S. PATENT DOCUMENTS

4,166,918	9/1979	Nostrand	136/89 R
4,385,971	3/1983	Swartz	204/129.1
4,451,970	6/1984	Lee	29/574
4,471,036	9/1984	Skothelm	428/111
4,488,349	12/1984	Murakami	29/395
4,510,674	4/1985	Iru	29/574

metal layer on the substrate, an amorphous and a transparent conductive layer. The includes anodic etching of exposed portions layer after deposition of the amorphous prior to depositing the transparent conduct

20 Claims, 2 Drawing Sheets

Details Text Image HTML KWIC

25	<input type="checkbox"/>	US 5107242	19920	Voltage non-linea
	<input type="checkbox"/>	A	421	resistor for gapp
26	<input type="checkbox"/>	US 5055416	19911	Electrolytic etch
	<input type="checkbox"/>	A	008	preventing electr

Details Text Image HTML Full

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10/19/02

US Full Image

US-PAT-NO: 5873203

DOCUMENT-IDENTIFIER: US 5873203 A

TITLE: Photoelectrolytically-desiccating multiple-glazed window units

----- KWIC -----

DATE FILED - AD (1):

19970902

Brief Summary Text - BSTX (10):

For example, a presently available sealed unit of the type referred to as a "glass on glass" or "welded edge" unit referred to above prevents moisture accumulation in the airspace by welding edges of glass sheets to each other, and filling the airspace between the welded sheets with a dry, insulating gas. Such a unit typically does not include a desiccant. One example of such a unit

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13	<input type="checkbox"/>	US 5873203	19990	Photoelectrolytic
	<input type="checkbox"/>	A	223	iccating multiple
14	<input type="checkbox"/>	US 5837178	19981	Method of manufac
	<input type="checkbox"/>	A	117	varistor precurs

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FIG. 1

FIG. 2

FIG. 3

FIG. 4

